

100V, 400A, 1.0mΩ N-channel Power SGT MOSFET

HMS400N10LL

Features

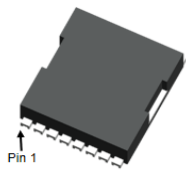
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant

Applications

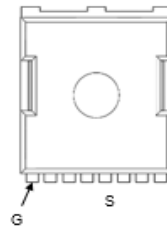
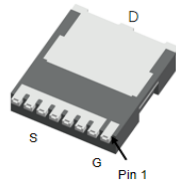
- Load Switch
- PWM Application
- Power Management

Product Summary

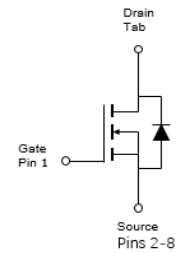
Parameters	Value	Unit
V_{DSS}	100	V
$V_{GS(th)}_{Typ}$	2.9	V
$I_D(@V_{GS}=10V)$	400	A
$R_{DS(ON)}_{Typ}(@V_{GS}=10V)$	1.0	mΩ



PowerJE®10x12



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
HMS400N10LL	SH1001M	1	Tape&Reel	PowerJE®10x12	2000	10000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	A
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	1987	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	33	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.35	°C/W

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	2.9	3.8	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 20A	-	1.0	1.3	mΩ
Dynamic Characteristics						
R _g	Gate Resistance	f = 1MHz	-	3.8	-	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz	9543	13360	18036	pF
C _{oss}	Output Capacitance		3652	5113	6902	pF
C _{rss}	Reverse Transfer Capacitance		87	122	164	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 50V, I _D = 20A	155	217	293	nC
Q _{gs}	Gate Source Charge		47	65	88	nC
Q _{gd}	Gate Drain("Miller") Charge		41	57	77	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 50V I _D = 20A, R _{GEN} = 3Ω	-	41	-	ns
t _r	Turn-On Rise Time		-	69	-	ns
t _{d(off)}	Turn-Off DelayTime		-	157	-	ns
t _f	Turn-Off Fall Time		-	92	-	ns
Body Diode Characteristics						
I _S	Maximum Continuous Body Diode Forward Current		-	-	400	A
I _{SM}	Maximum Pulsed Body Diode Forward Current		-	-	1200	A
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 20A, di/dt = 100A/us	93	130	176	ns
Qrr	Body Diode Reverse Recovery Charge		-	374	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 3\text{mH}$, $I_{AS} = 36.4\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Performance Characteristics

Figure 1: Power De-rating

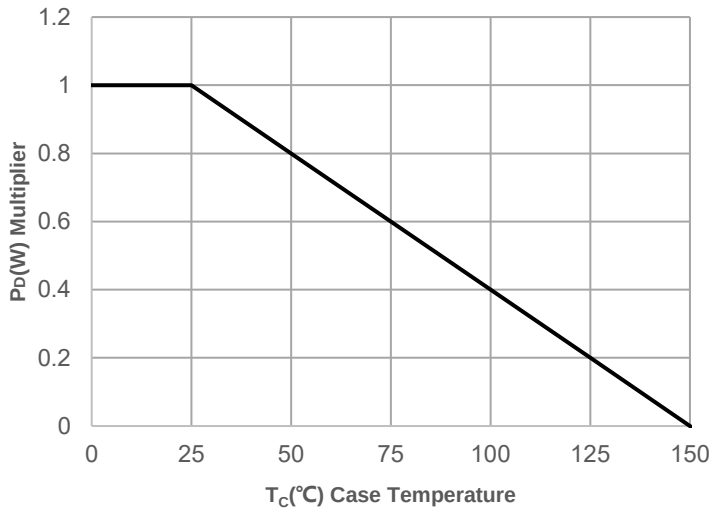


Figure 2: Current De-rating

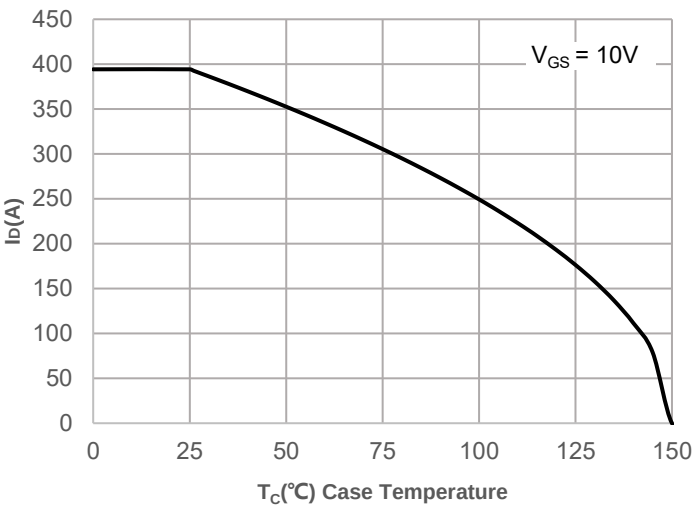


Figure 3: Normalized Maximum Transient Thermal Impedance

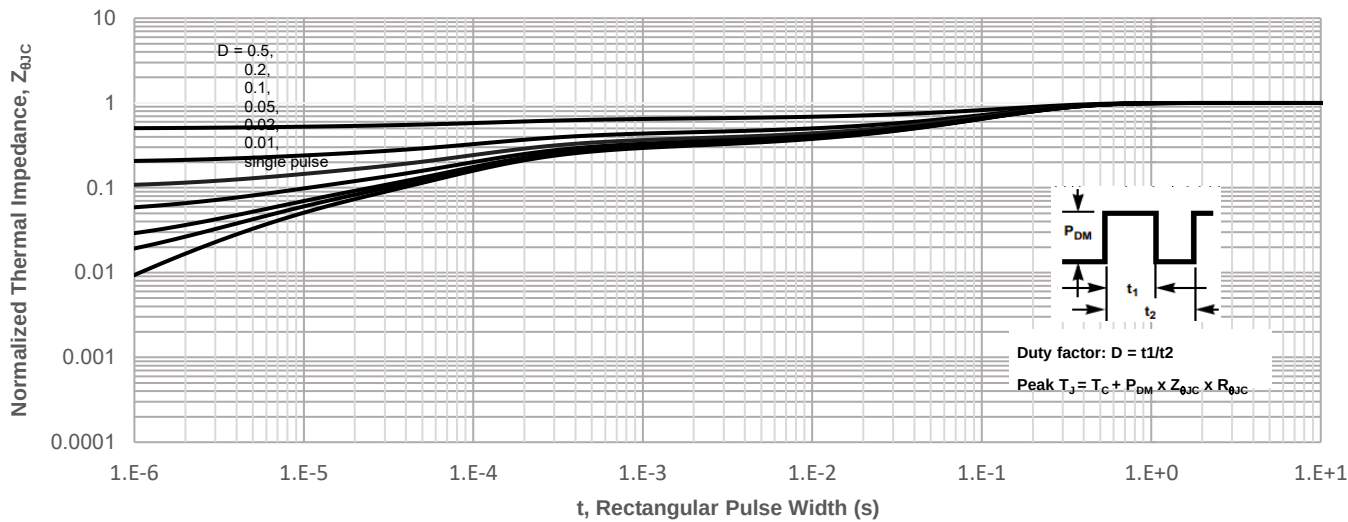
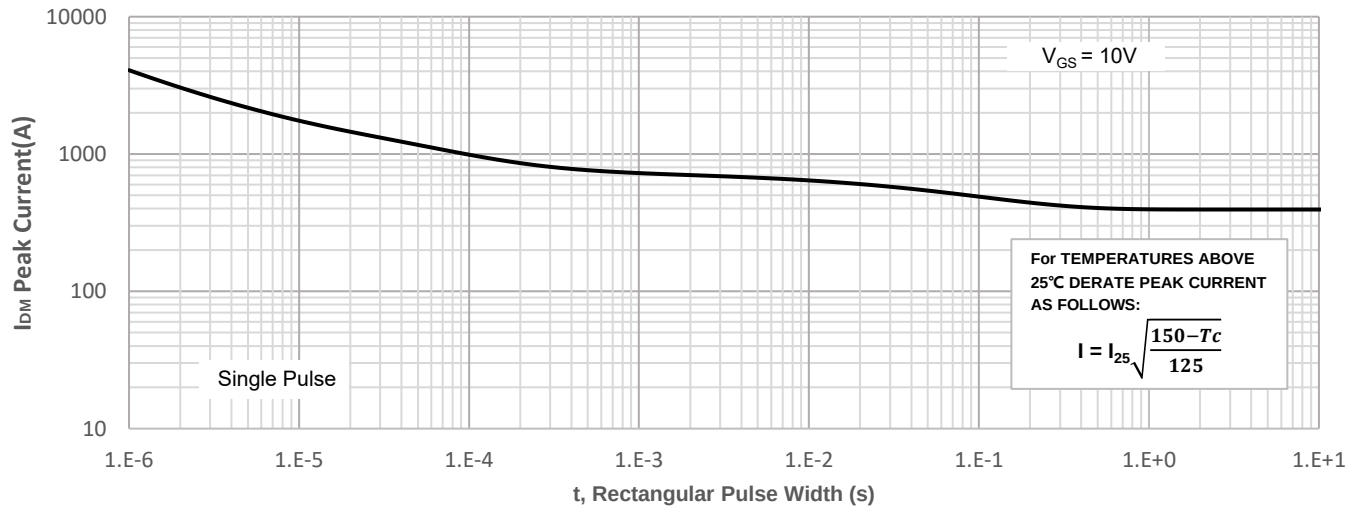


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

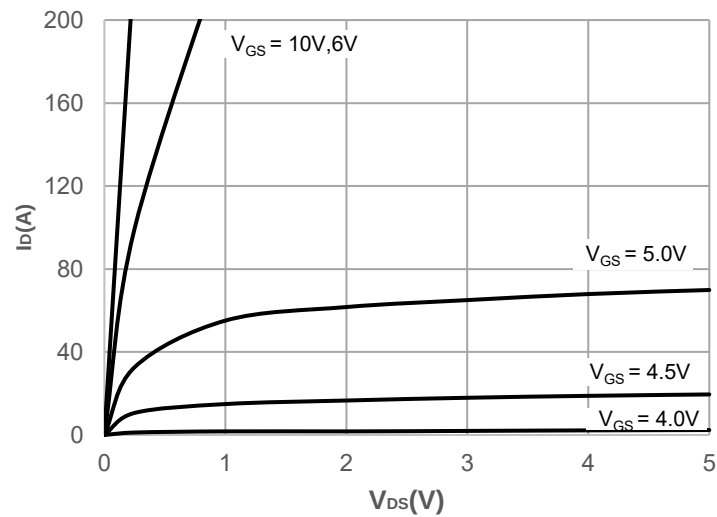


Figure 6: Typical Transfer Characteristics

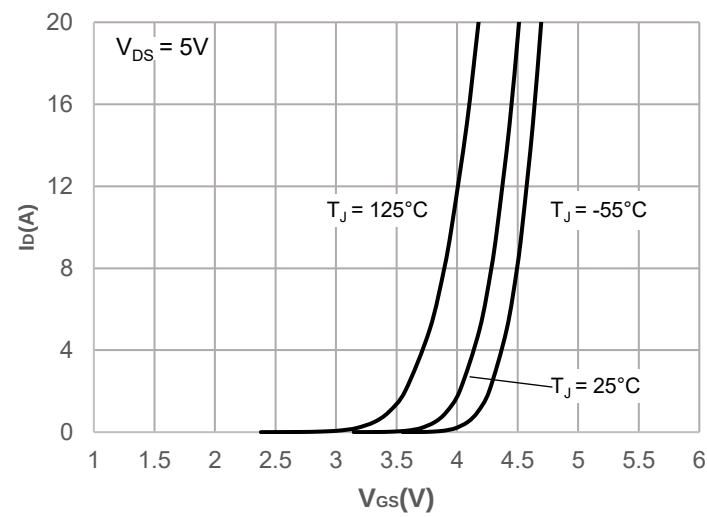


Figure 7: On-resistance vs. Drain Current

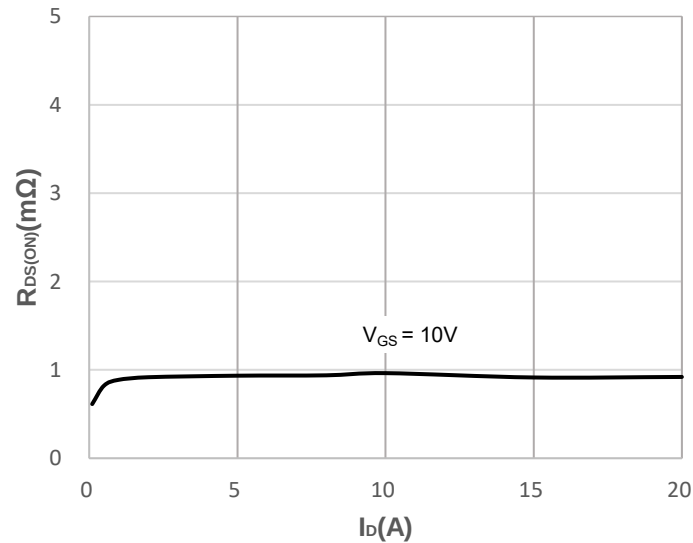


Figure 8: Body Diode Characteristics

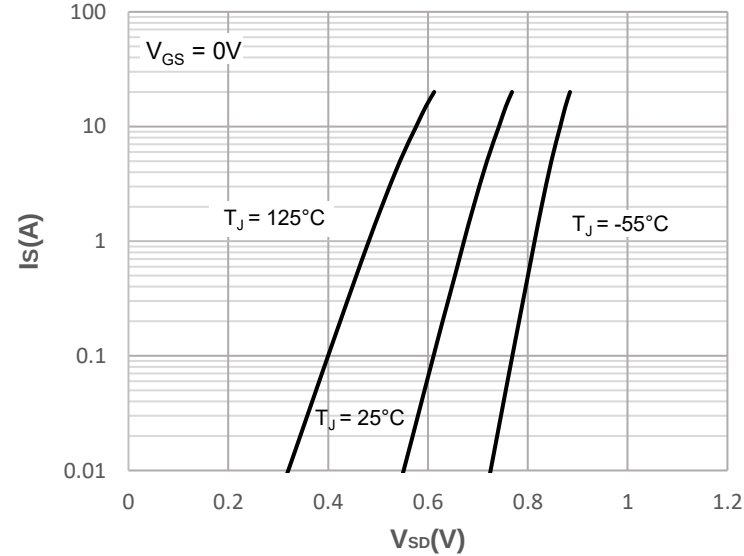


Figure 9: Gate Charge Characteristics

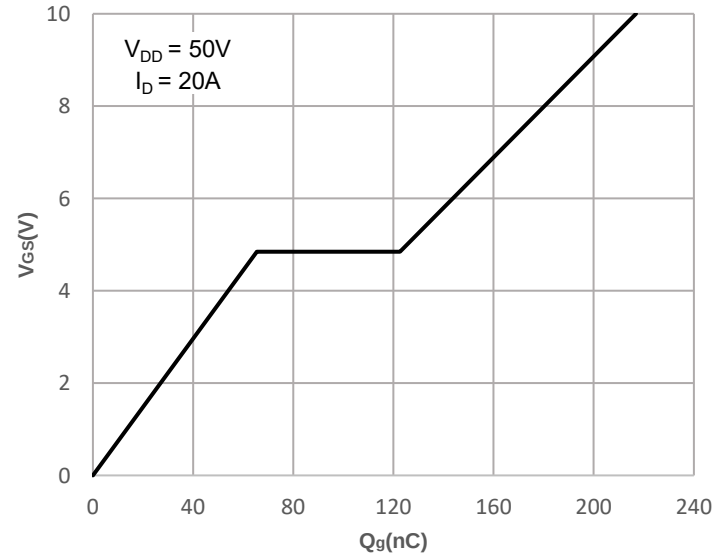
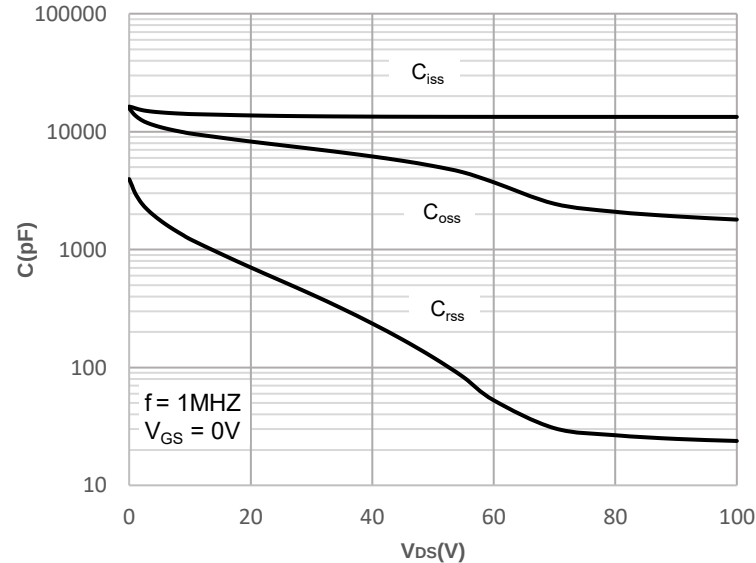


Figure 10: Capacitance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

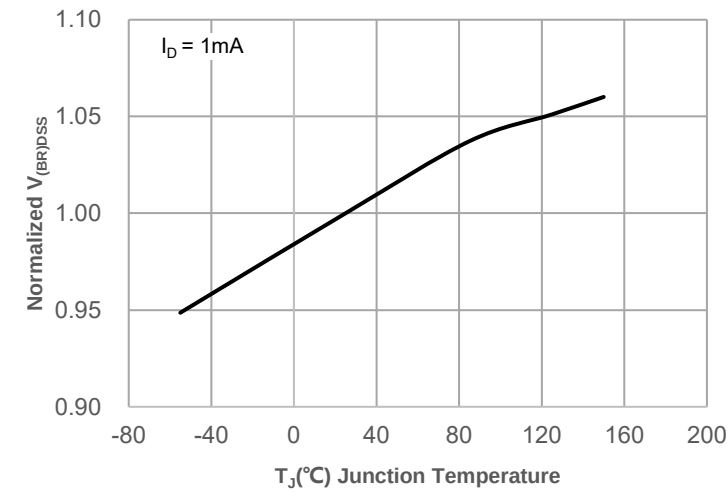


Figure 12: Normalized on Resistance vs. Junction Temperature

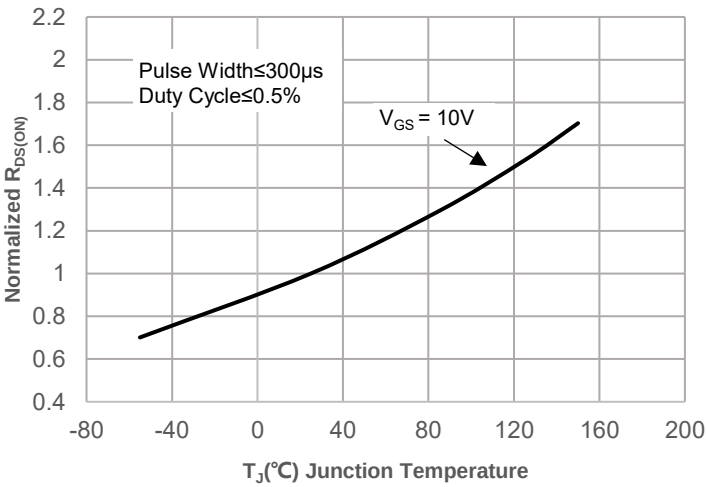


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

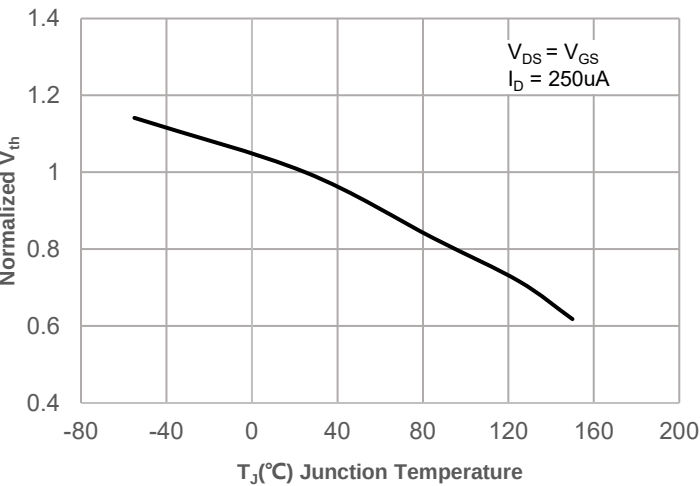


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

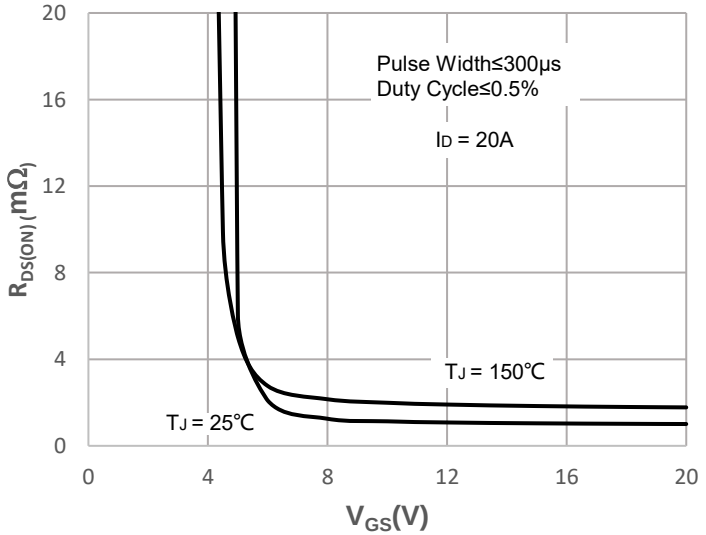
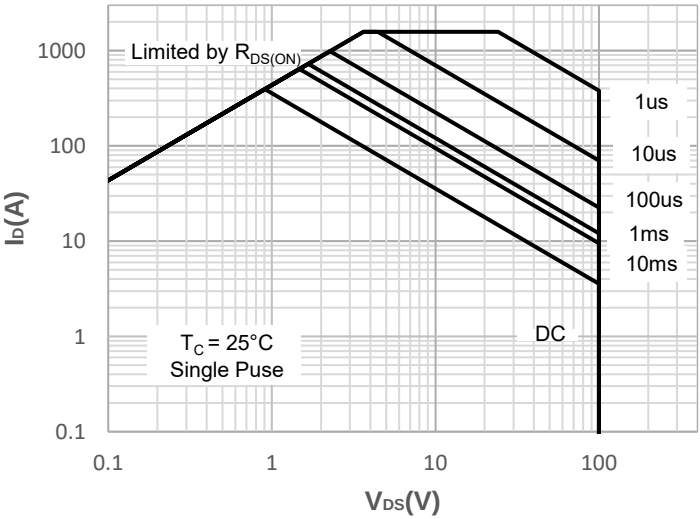


Figure 15: Maximum Safe Operating Area



Test Circuit

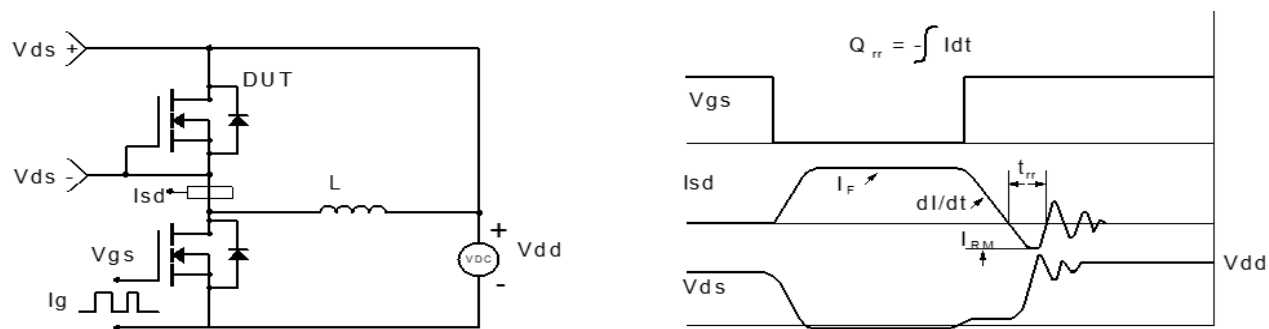
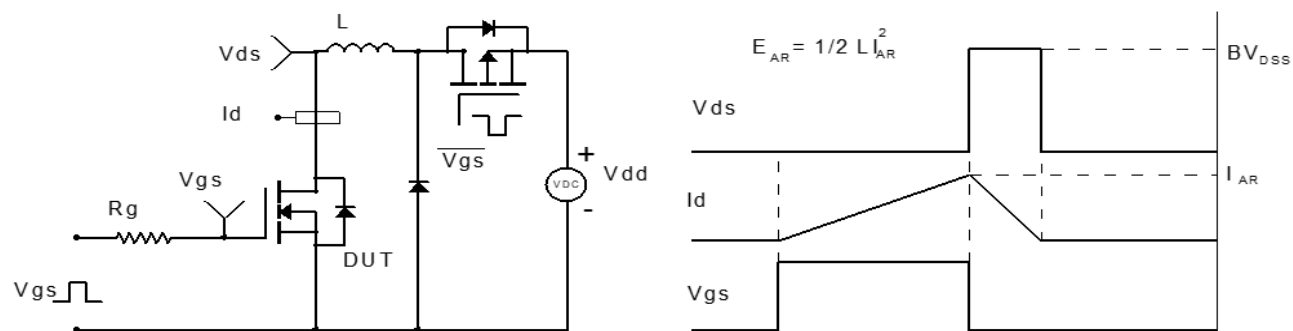
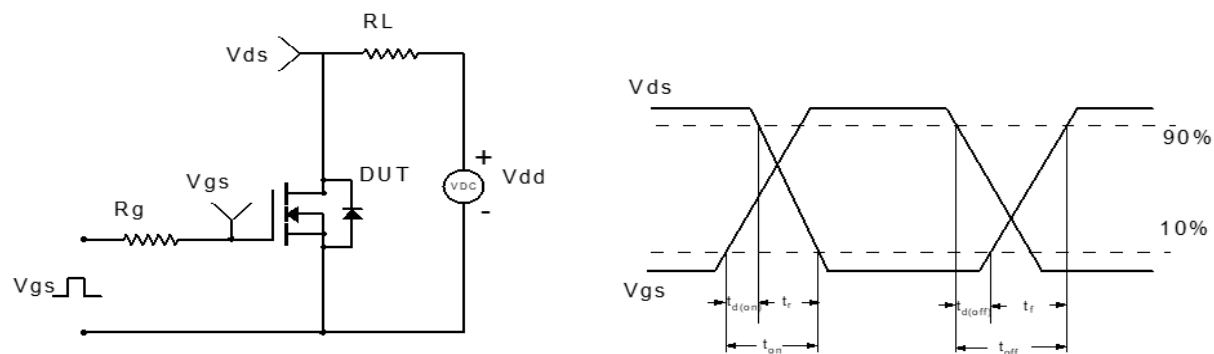
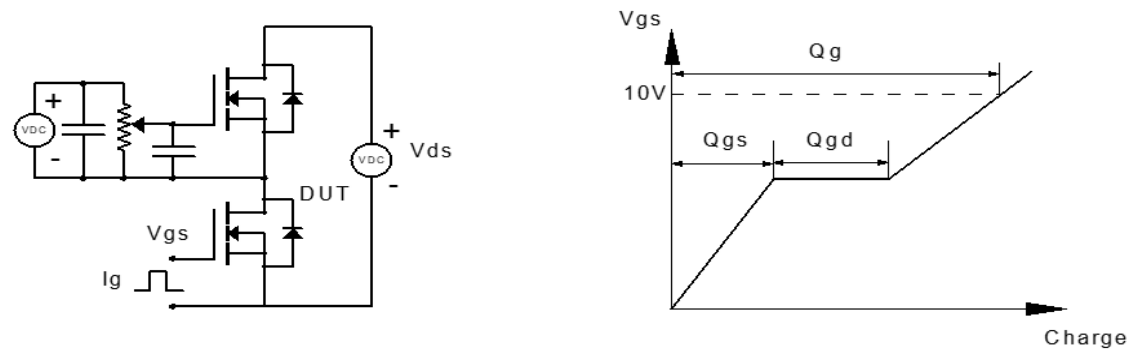


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PowerJE®10x12)

